



THE DATASHEET OF AOK20N60L



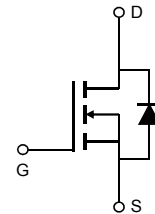
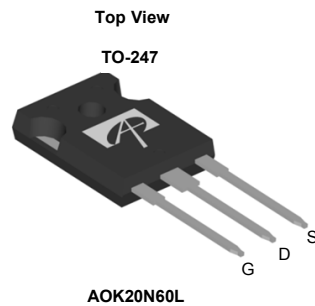
General Description

The AOK20N60L is fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications. By providing low $R_{DS(on)}$, C_{iss} and C_{rss} along with guaranteed avalanche capability this parts can be adopted quickly into new and existing offline power supply designs.

Product Summary

V_{DS}	700V@150°C
I_D (at $V_{GS}=10V$)	20A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 0.37Ω

100% UIS Tested
 100% R_g Tested



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	AOK20N60L	Units
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	±30	V
Continuous Drain Current	I_D	$T_C=25^\circ C$	20
		$T_C=100^\circ C$	12
Pulsed Drain Current ^C	I_{DM}	80	A
Avalanche Current ^C	I_{AR}	6.5	A
Repetitive avalanche energy ^C	E_{AR}	630	mJ
Single plused avalanche energy ^G	E_{AS}	1260	mJ
Peak diode recovery dv/dt	dv/dt	5	V/ns
Power Dissipation ^B	P_D	$T_C=25^\circ C$	417
		Derate above 25°C	3.3
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	T_L	300	°C

Thermal Characteristics

Parameter	Symbol	AOK20N60L	Units
Maximum Junction-to-Ambient ^{A,D}	$R_{\theta JA}$	40	°C/W
Maximum Case-to-sink ^A	$R_{\theta CS}$	0.5	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	0.3	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V, T _J =25°C	600			V
		I _D =250μA, V _{GS} =0V, T _J =150°C		700		
BV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D =250μA, V _{GS} =0V		0.8		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =600V, V _{GS} =0V			1	μA
		V _{DS} =480V, T _J =125°C			10	
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±30V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =5V, I _D =250μA	3.2	3.8	4.5	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =10A		0.29	0.37	Ω
g _{FS}	Forward Transconductance	V _{DS} =40V, I _D =10A		25		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.69	1	V
I _S	Maximum Body-Diode Continuous Current				20	A
I _{SM}	Maximum Body-Diode Pulsed Current				80	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =25V, f=1MHz	2448	3061	3680	pF
C _{oss}	Output Capacitance		190	273	360	pF
C _{rss}	Reverse Transfer Capacitance		13	22.8	35	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.7	1.4	2.1	Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =480V, I _D =20A	48	61	74	nC
Q _{gs}	Gate Source Charge		14	18	22	nC
Q _{gd}	Gate Drain Charge		12	24	36	nC
t _{D(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =300V, I _D =20A, R _G =25Ω		57		ns
t _r	Turn-On Rise Time			125		ns
t _{D(off)}	Turn-Off Delay Time			128		ns
t _f	Turn-Off Fall Time			88		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, di/dt=100A/μs, V _{DS} =100V	384	480	580	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, di/dt=100A/μs, V _{DS} =100V	8	10.5	13	μC

A. The value of R_{θJA} is measured with the device in a still air environment with T_A=25°C.

B. The power dissipation P_D is based on T_{J(MAX)}=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J=25°C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150°C. The SOA curve provides a single pulse rating.

G. L=60mH, I_{AS}=6.5A, V_{DD}=150V, R_G=25Ω, Starting T_J=25°C

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

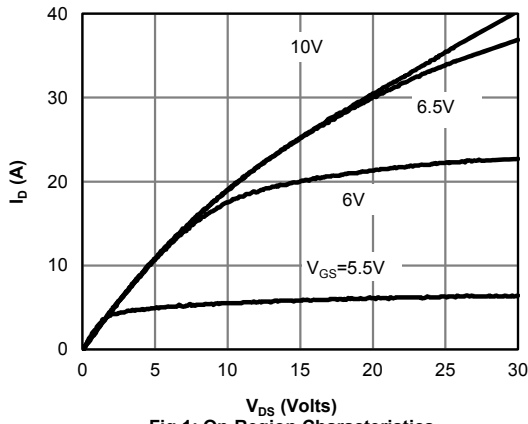


Fig 1: On-Region Characteristics

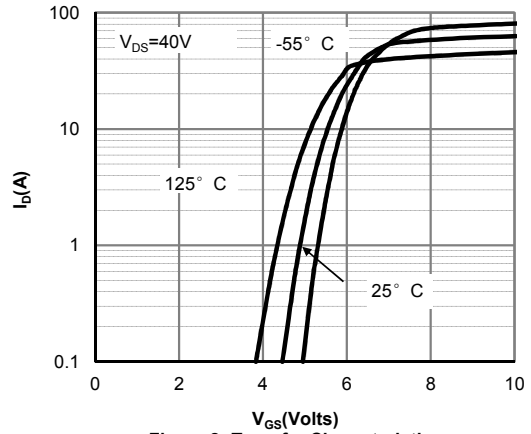


Figure 2: Transfer Characteristics

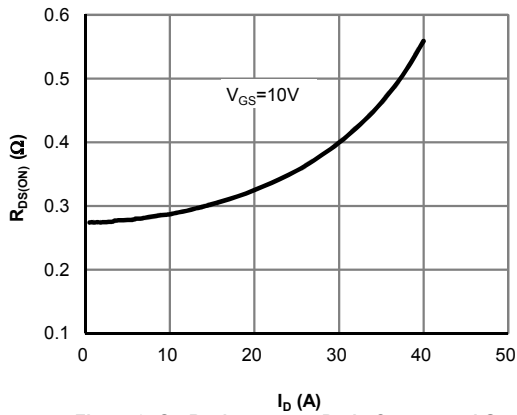


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

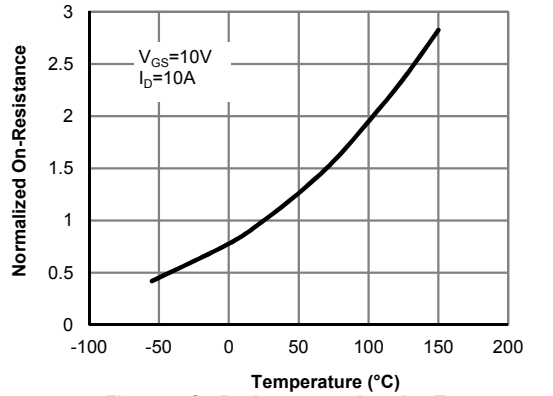


Figure 4: On-Resistance vs. Junction Temperature

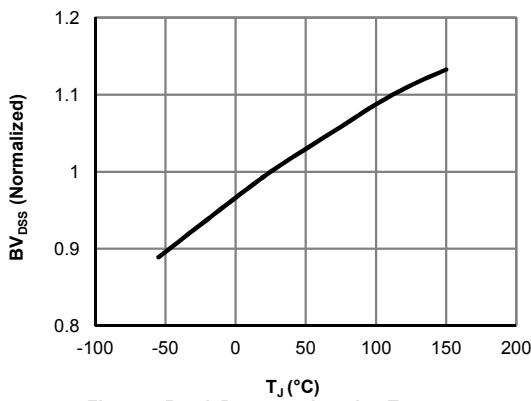


Figure 5: Break Down vs. Junction Temperature

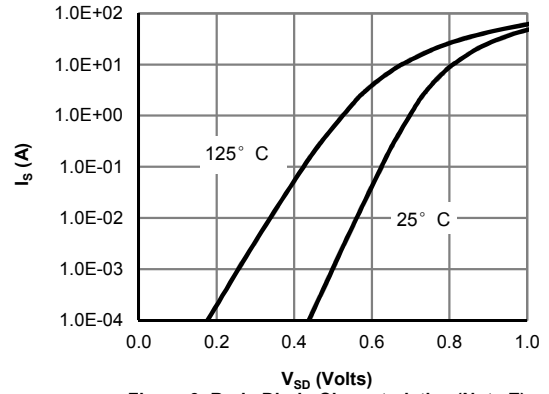


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

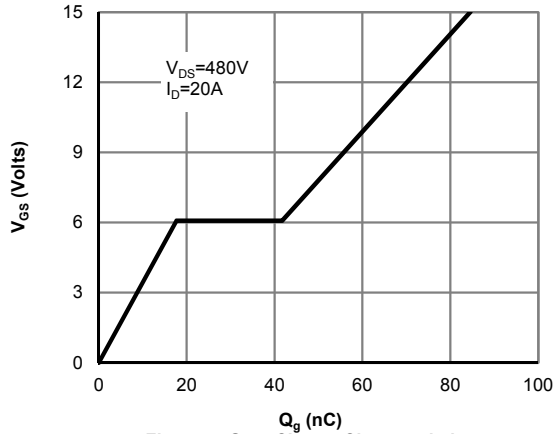


Figure 7: Gate-Charge Characteristics

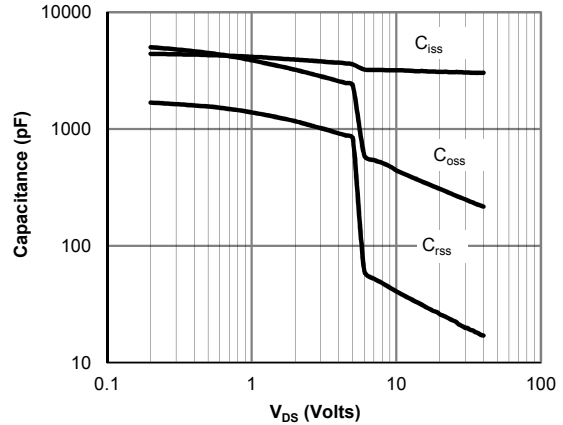


Figure 8: Capacitance Characteristics

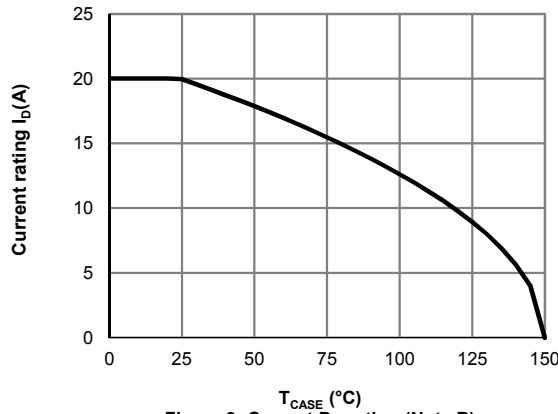


Figure 9: Current De-rating (Note B)

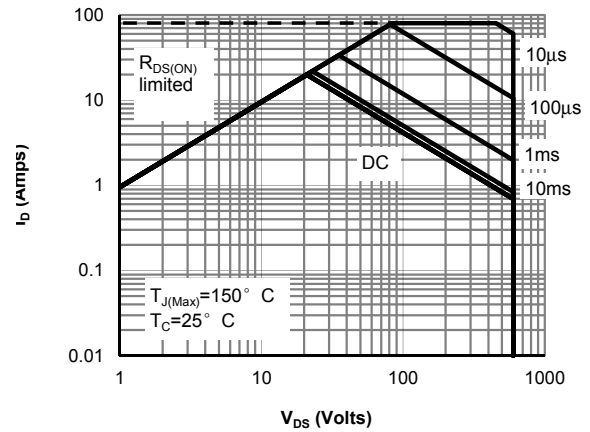


Figure 10: Maximum Forward Biased Safe Operating Area for AOK20N60L (Note F)

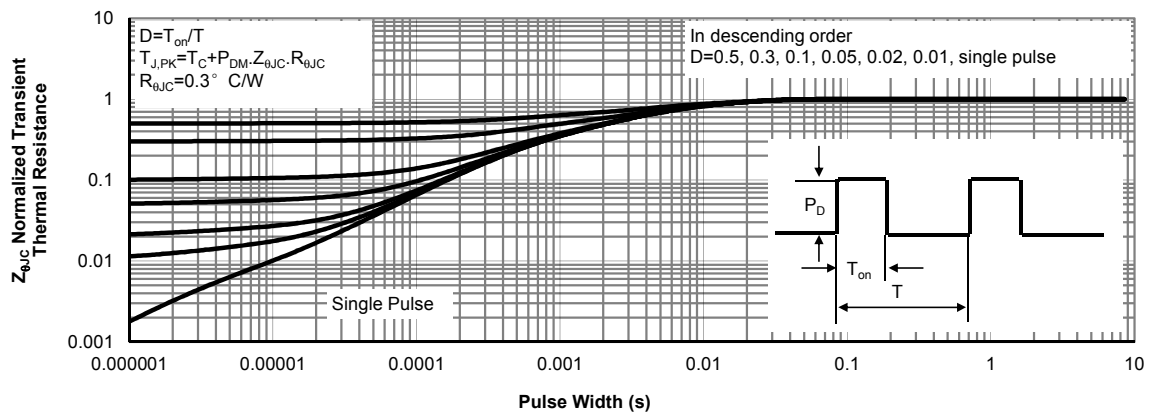
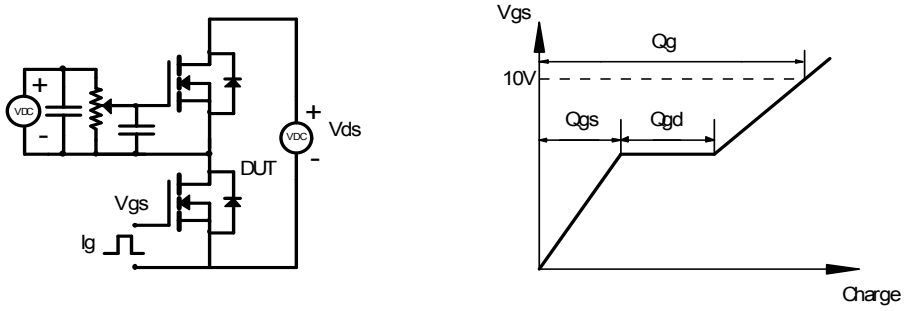
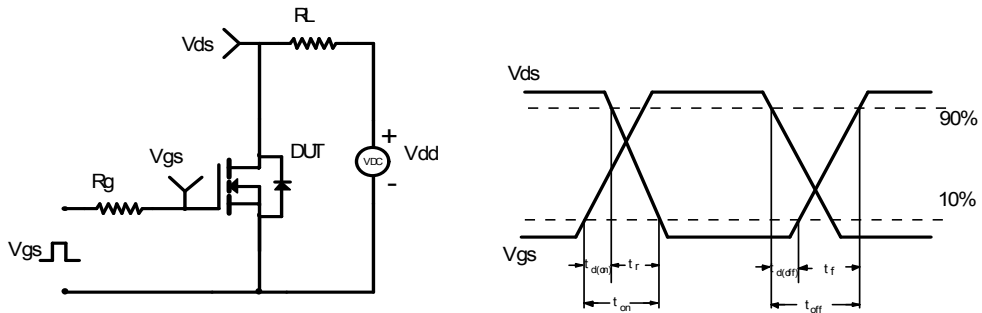


Figure 11: Normalized Maximum Transient Thermal Impedance for AOK20N60L (Note F)

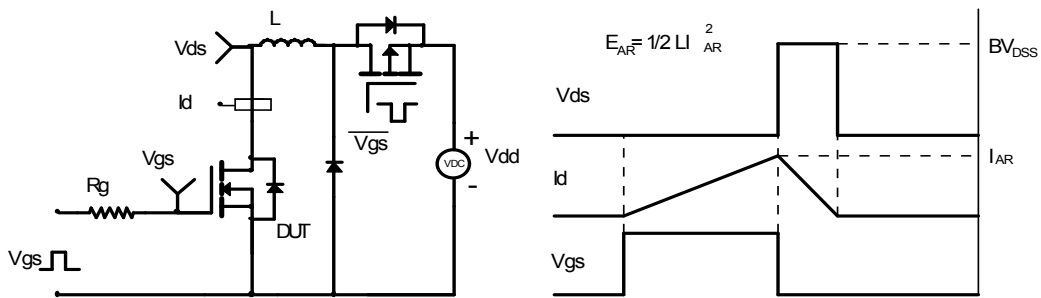
Gate Charge Test Circuit & Waveform



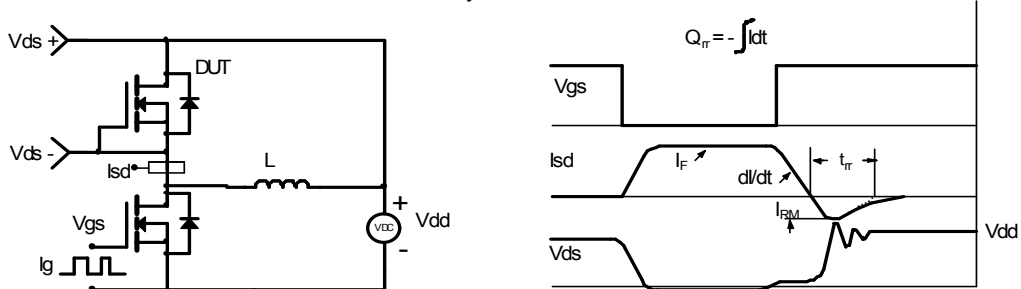
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



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